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SEMICONDUCTOR ENERGY LABORATORY CO.,
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(71) Applicant (for all designated States except US): SEMI-CONDUCTOR ENERGY LABORATORY CO., LTD.
[JP/JP]; 398, Hase, Atsugi-shi, Kanagawa, 2430036 (JP).

(72) Inventors; and

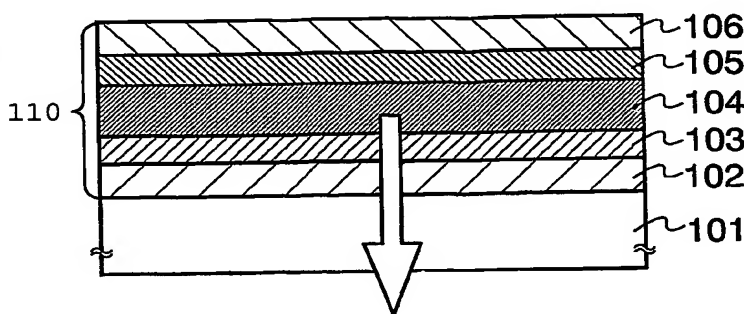
(75) Inventors/Applicants (for US only): IKEDA, Hisao [JP/JP]; c/o SEMICONDUCTOR ENERGY LABORATORY CO., LTD., 398, Hase, Atsugi-shi, Kanagawa, 2430036 (JP). SAKATA, Junichiro [JP/JP]; c/o SEMI-CONDUCTOR ENERGY LABORATORY CO., LTD., 398, Hase, Atsugi-shi, Kanagawa, 2430036 (JP). KU-MAKI, Daisuke [JP/-]. SEO, Satoshi [JP/JP]; c/o

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(54) Title: LIGHT EMITTING ELEMENT AND DISPLAY DEVICE USING THE SAME



(57) Abstract: An object of the invention is to provide a highly reliable light emitting element with low drive voltage and longer life than a conventional light emitting element, and a display device using the light emitting element. A light emitting element according to the invention comprises a plurality of layers which is interposed between a pair of electrodes, in which at least one of the plurality of layers is formed of a layer containing a light emitting material, and the layer containing a light emitting material is

interposed between a layer containing an oxide semiconductor and/or metal oxide and a material having a higher hole transporting property than an electron transporting property, and a layer containing an oxide semiconductor and/or metal oxide, a material having a higher electron transporting property than a hole transporting property and a material which can donate electrons to the material having a higher electron transporting property than a hole transporting property.

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